

Unprecedented uniform 3D growth integration of 10-layer stacked Si nanowires on tightly confined sidewall grooves

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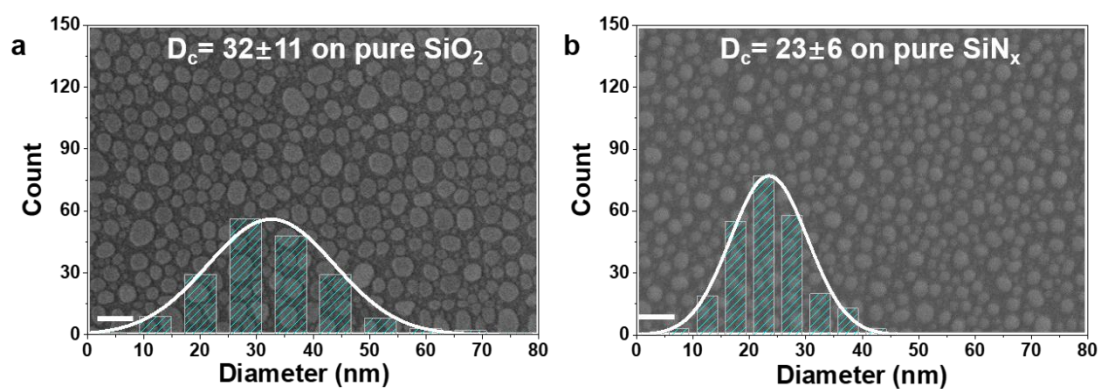


Figure S1. SEM images and catalyst size distribution statistics of the In droplets deposited via EBE evaporation upon the (a) SiO₂ and (b) SiN_x substrates.

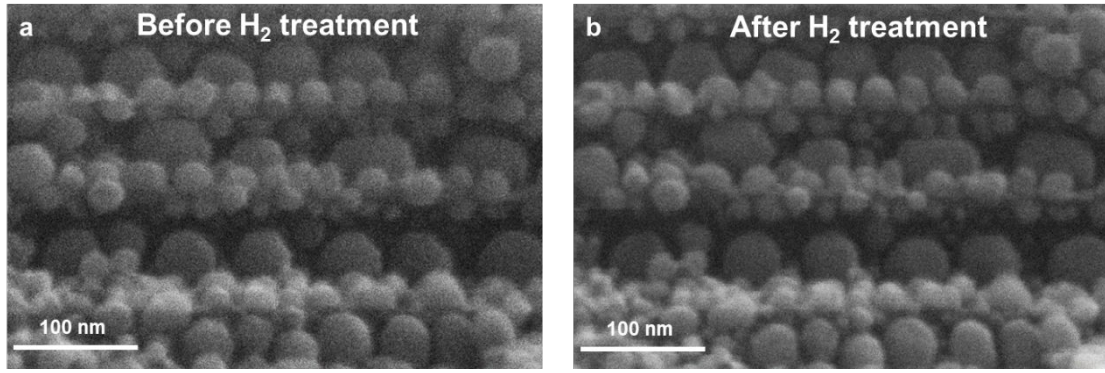


Figure S2. (a) and (b) show SEM images of the In droplets evaporated on the hetero-SiO₂/SiN_x sidewall grooves before and after H₂ plasma treatment, respectively.

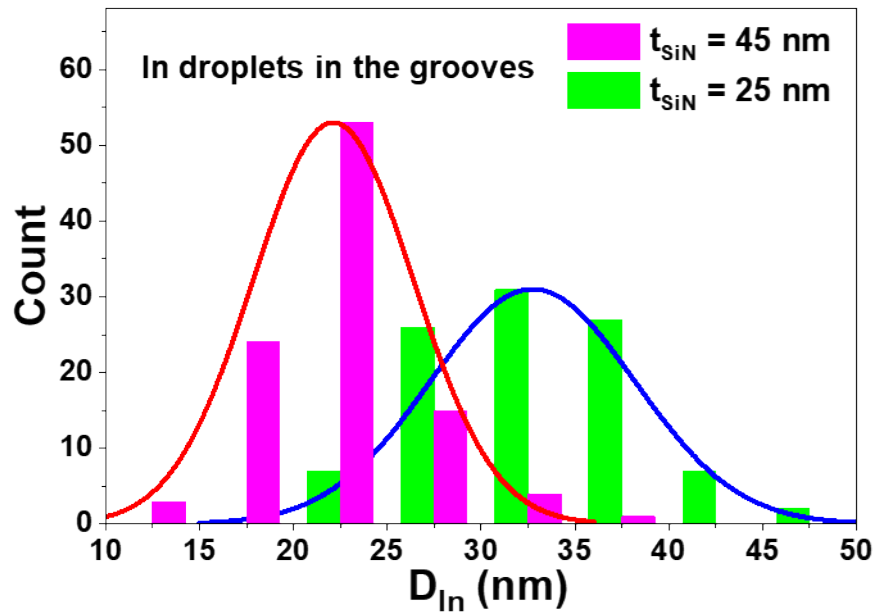


Figure S3. Statistics on the diameter distributions of the In droplets formed in the grooves with different SiN_x edge thicknesses.